The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1.-24. (Canceled)

25. (Currently Amended) A device having at least one display device, said display device comprising:

a glass substrate having an insulating surface;

at least one thin film transistor formed over said glass substrate, said thin film transistor including at least a channel region, source and drain regions with said channel region therebetween, a gate insulating film adjacent to said channel region, and a gate electrode adjacent to said channel region with said gate insulating film interposed therebetween;

a first signal line extending in a first direction over said substrate, said first signal line being contiguous to said gate electrode;

an interlayer insulating film covering said thin film transistor;

a lead electrode ~~comprising aluminum~~ formed over said interlayer insulating film and electrically connected to one of the source or drain regions of said thin film transistor through a first hole of said interlayer insulating film;

a second signal line formed over said interlayer insulating film and extending ~~in a second direction orthogonal to~~ across said first direction, said second signal line ~~comprising aluminum and~~ being electrically connected to the other one of the source or drain regions;

an organic resin film formed over the thin film transistor, said interlayer insulating film and said lead electrode to provide a leveled upper surface; and

a pixel electrode formed over said organic resin film, said pixel electrode being electrically connected to said one of the source or drain regions of said thin film transistor via said lead electrode and through a second hole of the organic resin film,

wherein the first hole and the second hole do not overlap to each other, and

wherein a blocking film comprising silicon oxide is interposed between said glass substrate and said thin film transistor.

26.-42. (Canceled)

43. (Previously Presented) The device according to claim 25 wherein said display panel is a liquid crystal device.

44.- 66. (Canceled)

67. (Currently Amended) A computer comprising at least one display device, said display device comprising:

a glass substrate having an insulating surface;

at least one thin film transistor formed over said glass substrate, said thin film transistor including at least a channel region, source and drain regions with said channel region therebetween, a gate insulating film adjacent to said channel region, and a gate electrode adjacent to said channel region with said gate insulating film interposed therebetween;

a first signal line extending in a first direction over said substrate, said first signal line being contiguous to said gate electrode;

an interlayer insulating film covering said thin film transistor;

a lead electrode ~~comprising aluminum~~ formed over said interlayer insulating film and electrically connected to one of the source or drain regions of said thin film transistor through a first hole of said interlayer insulating film;

a second signal line formed over said interlayer insulating film and extending ~~in a second direction orthogonal to~~ across said first direction, said second signal line ~~comprising aluminum and~~ electrically connected to the other one of the source or drain regions;

an organic resin film formed over the thin film transistor, said interlayer insulating film and said lead electrode to provide a leveled upper surface; and

a pixel electrode formed over said organic resin film, said pixel electrode being electrically connected to said one of the source or drain regions of the thin film transistor via said lead electrode and through a second hole of the organic resin film,

wherein the first hole and the second hole do not overlap to each other, and

wherein a blocking film comprising silicon oxide is interposed between said glass substrate and said thin film transistor.

68. (Canceled)

69. (New) The device according to claim 25 wherein said first signal line comprises aluminum.

70. (New) The device according to claim 25 wherein said second signal line comprises aluminum.

71. (New) The device according to claim 25 wherein said organic resin film comprises polyimide.

72. (New) The device according to claim 25 wherein said semiconductor layer comprises crystalline silicon.

73. (New) A television comprising:

a tuner for receiving television radio wave;

a display device operationally connected to said tuner, said display device having a plurality of pixels, each of which comprising:

at least one thin film transistor formed over a glass substrate, said thin film transistor including at least a channel region, source and drain regions with said channel region therebetween, a gate insulating film adjacent to said channel region, and a gate electrode adjacent to said channel region with said gate insulating film interposed therebetween;

a first signal line extending in a first direction over said substrate, said first signal line being contiguous to said gate electrode;

an interlayer insulating film covering said thin film transistor;

a lead electrode formed over said interlayer insulating film and electrically connected to one of the source or drain regions of said thin film transistor through a first hole of said interlayer insulating film;

a second signal line formed over said interlayer insulating film and extending across said first direction, said second signal line being electrically connected to the other one of the source or drain regions;

an organic resin film formed over the thin film transistor, said interlayer insulating film and said lead electrode to provide a leveled upper surface; and

a pixel electrode formed over said organic resin film, said pixel electrode being electrically connected to said one of the source or drain regions of said thin film transistor via said lead electrode and through a second hole of the organic resin film,

wherein the first hole and the second hole do not overlap to each other, and

wherein a blocking film comprising silicon oxide is interposed between said glass substrate and said thin film transistor.

74. (New) The television according to claim 73 wherein said first signal line comprises aluminum.

75. (New) The television according to claim 73 wherein said second signal line comprises aluminum.

76. (New) The television according to claim 73 wherein said organic resin film comprises polyimide.

77. (New) The television according to claim 73 wherein said semiconductor layer comprises crystalline silicon.

78. (New) The computer according to claim 67 wherein said first signal line comprises aluminum.

79. (New) The computer according to claim 67 wherein said second signal line comprises aluminum.

80. (New) The computer according to claim 67 wherein said organic resin film comprises polyimide.

81. (New) The computer according to claim 67 wherein said semiconductor layer comprises crystalline silicon.

82. (New) The computer according to claim 67 wherein said display device is a liquid crystal device.

83. (New) The television according to claim 73 wherein said display device is a liquid crystal device.

84. (New) The device according to claim 25 further comprising a second thin film transistor electrically connected to said pixel electrode, said second thin film transistor having an opposite conductivity type to said at least one thin film transistor.

85. (New) A device having at least one display device, said display device comprising:

a glass substrate having an insulating surface;

at least one thin film transistor formed over said glass substrate, said thin film transistor including at least a channel region, source and drain regions with said channel region therebetween, a gate insulating film adjacent to said channel region, and a gate electrode adjacent to said channel region with said gate insulating film interposed therebetween;

a first signal line extending in a first direction over said substrate, said first signal line being contiguous to said gate electrode;

an interlayer insulating film covering said thin film transistor;

a lead electrode formed over said interlayer insulating film and electrically connected to one of the source or drain regions of said thin film transistor through a first hole of said interlayer insulating film;

a second signal line formed over said interlayer insulating film and extending across said first direction, said second signal line being electrically connected to the other one of the source or drain regions;

an organic resin film formed over the thin film transistor, said interlayer insulating film and said lead electrode to provide a leveled upper surface; and

a pixel electrode formed over said organic resin film, said pixel electrode being electrically connected to said lead electrode through a second hole of the organic resin film,

wherein a contact surface between the lead electrode and said one of the source and drain regions does not overlap with a contact surface between the lead electrode and the pixel electrode,

the first hole and the second hole do not overlap to each other, and

wherein a blocking film comprising silicon oxide is interposed between said glass substrate and said thin film transistor.

86. (New) The device according to claim 85 wherein said first signal line comprises aluminum.

87. (New) The device according to claim 85 wherein said second signal line comprises aluminum.

88. (New) The device according to claim 85 wherein said organic resin film comprises polyimide.

89. (New) The device according to claim 85 wherein said semiconductor layer comprises crystalline silicon.

90. (New) A computer comprising at least one display device, said display device comprising:

a glass substrate having an insulating surface;

at least one thin film transistor formed over said glass substrate, said thin film transistor including at least a channel region, source and drain regions with said channel region therebetween, a gate insulating film adjacent to said channel region, and

a gate electrode adjacent to said channel region with said gate insulating film interposed therebetween;

a first signal line extending in a first direction over said substrate, said first signal line being contiguous to said gate electrode;

an interlayer insulating film covering said thin film transistor;

a lead electrode formed over said interlayer insulating film and electrically connected to one of the source or drain regions of said thin film transistor through a first hole of said interlayer insulating film;

a second signal line formed over said interlayer insulating film and extending across said first direction, said second signal line being electrically connected to the other one of the source or drain regions;

an organic resin film formed over the thin film transistor, said interlayer insulating film and said lead electrode to provide a leveled upper surface; and

a pixel electrode formed over said organic resin film, said pixel electrode being electrically connected to said lead electrode through a second hole of the organic resin film,

wherein a contact surface between the lead electrode and said one of the source and drain regions does not overlap with a contact surface between the lead electrode and the pixel electrode,

the first hole and the second hole do not overlap to each other, and

wherein a blocking film comprising silicon oxide is interposed between said glass substrate and said thin film transistor.

91. (New) The computer according to claim 90 wherein said first signal line comprises aluminum.

92. (New) The computer according to claim 90 wherein said second signal line comprises aluminum.

93. (New) The computer according to claim 90 wherein said organic resin film comprises polyimide.

94. (New) The computer according to claim 90 wherein said semiconductor layer comprises crystalline silicon.

95. (New) A television comprising:

a tuner for receiving television radio wave;

a display device operationally connected to said tuner, said display device having a plurality of pixels, each of which comprising:

at least one thin film transistor formed over a glass substrate, said thin film transistor including at least a channel region, source and drain regions with said channel region therebetween, a gate insulating film adjacent to said channel region, and a gate electrode adjacent to said channel region with said gate insulating film interposed therebetween;

a first signal line extending in a first direction over said substrate, said first signal line being contiguous to said gate electrode;

an interlayer insulating film covering said thin film transistor;

a lead electrode formed over said interlayer insulating film and electrically connected to one of the source or drain regions of said thin film transistor through a first hole of said interlayer insulating film;

a second signal line formed over said interlayer insulating film and extending across said first direction, said second signal line being electrically connected to the other one of the source or drain regions;

an organic resin film formed over the thin film transistor, said interlayer insulating film and said lead electrode to provide a leveled upper surface; and

a pixel electrode formed over said organic resin film, said pixel electrode being electrically connected to said lead electrode through a second hole of the organic resin film,

wherein a contact surface between the lead electrode and said one of the source and drain regions does not overlap with a contact surface between the lead electrode and the pixel electrode,

the first hole and the second hole do not overlap to each other, and

wherein a blocking film comprising silicon oxide is interposed between said glass substrate and said thin film transistor.

96. (New) The television according to claim 95 wherein said first signal line comprises aluminum.

97. (New) The television according to claim 95 wherein said second signal line comprises aluminum.

98. (New) The television according to claim 95 wherein said organic resin film comprises polyimide.

99. (New) The television according to claim 95 wherein said semiconductor layer comprises crystalline silicon.